

Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claim 1 (Canceled)

Claim 2 (Currently Amended): ~~[[The]]~~ A semiconductor device ~~according to claim 1~~
comprising:

a semiconductor chip which includes a circuit element, a first wiring and an electrode pad, wherein the circuit element includes an electronic element, and wherein the first wiring is electrically connected between the circuit element to the electrode pad;

an insulating layer formed on the semiconductor chip, wherein the insulating layer has an opening which is aligned over the electrode pad;

an external terminal formed on the insulating layer;

a second wiring formed on the insulating layer, wherein the second wiring electrically connects the electrode pad to the external terminal via the opening; and

a shielding film located in a same plane as the first wiring and interposed between the electronic element and the second wiring,

wherein the electronic element includes a capacitor, and wherein the shielding film completely overlaps the capacitor.

Claim 3 (Currently Amended): ~~[[The]]~~ A semiconductor device according to claim 1
comprising:

a semiconductor chip which includes a circuit element, a first wiring and an
electrode pad, wherein the circuit element includes an electronic element, and wherein
the first wiring is electrically connected between the circuit element to the electrode pad;

an insulating layer formed on the semiconductor chip, wherein the insulating
layer has an opening which is aligned over the electrode pad;

an external terminal formed on the insulating layer;

a second wiring formed on the insulating layer, wherein the second wiring
electrically connects the electrode pad to the external terminal via the opening; and

a shielding film located in a same plane as the first wiring and interposed
between the electronic element and the second wiring,

wherein the shielding film is a metal and is connected to a ground voltage.

Claim 4 (Canceled)

Claim 5 (Currently Amended): ~~[[The]]~~ A semiconductor device according to claim 1
comprising:

a semiconductor chip which includes a circuit element, a first wiring and an
electrode pad, wherein the circuit element includes an electronic element, and wherein
the first wiring is electrically connected between the circuit element to the electrode pad;

an insulating layer formed on the semiconductor chip, wherein the insulating layer has an opening which is aligned over the electrode pad;

an external terminal formed on the insulating layer;

a second wiring formed on the insulating layer, wherein the second wiring electrically connects the electrode pad to the external terminal via the opening; and

a shielding film located in a same plane as the first wiring and interposed between the electronic element and the second wiring,

wherein the electrode pad is located in a peripheral region of the semiconductor device, and wherein the external terminal is located in a central region of the semiconductor device.

Claim 6 (Original): The semiconductor device according to claim 2, wherein the circuit element comprises a voltage controlled oscillator which includes the capacitor.

Claim 7 (Original): The semiconductor device according to claim 6, wherein the voltage controlled oscillator generates a signal having a frequency of at least 300 MHz.

Claims 8-17 (Canceled)

Claim 18 (Original): A semiconductor device comprising:

a semiconductor chip;

a first inductor formed on the semiconductor chip;
a first insulating layer formed on the semiconductor chip and the first inductor;
a first shielding film formed on the first insulating layer;
a second insulating layer formed on the first insulating layer and the first
shielding film;
a second shielding film formed on the second insulating layer;
a third insulating layer formed on the second insulating layer and the second
shielding film; and
a second inductor and an external terminal formed on the third insulating layer;
wherein the first inductor is located under the first shielding film and the second
shielding film is located under the second inductor.

Claim 19 (Original): The semiconductor device according to claim 18, wherein the first
shielding film and the second shielding film are a magnetic material.